

GBC817

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GBC817 is designed for switching and AF amplifier application, suitable for driver storages and low power output storages.

Package Dimensions

SOT - 23

Marking:

□ : hFE Rank Code

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	50	V
Collector to Emitter Voltage	VCEO	45	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	800	mA
Total Power Dissipation	PD	225	mW

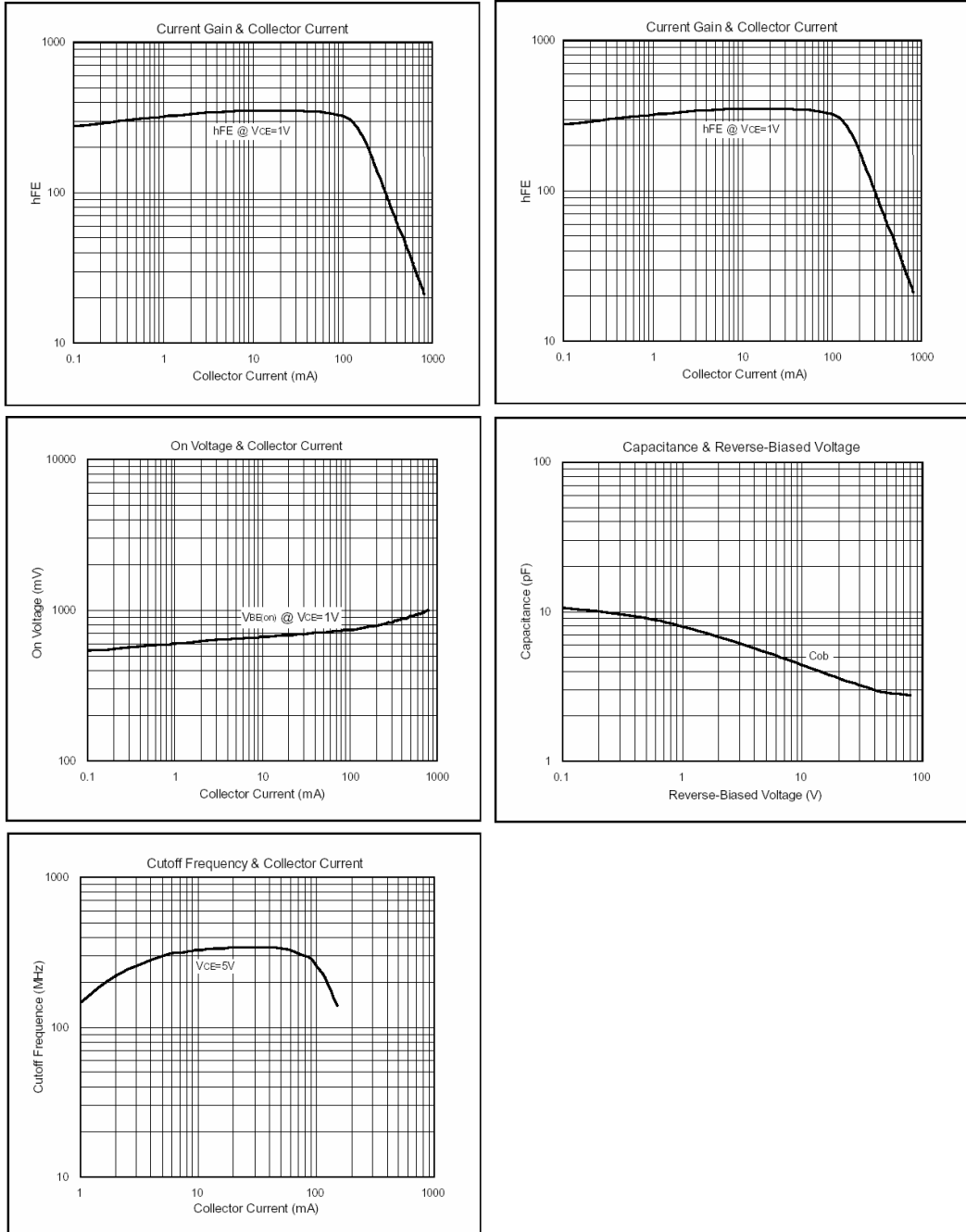
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVEBO	5	-	-	V	IE=-100uA
BVCEO	45	-	-	V	IC=10mA
BVCES	50	-	-	V	IC=100uA
ICES	-	-	100	nA	VCE=25V
IEBO	-	-	100	nA	VEB=4V
*VCE(sat)	-	-	700	mV	IC=500mA, IB=50mA
VBE(on)	-	-	1.2	V	VCE=1V, IC=300mA
hFE	100	-	630		VCE=1V, IC=100mA
fT	-	100	-	MHz	VCE=5V, IC=10mA, f=100MHz
Cob	-	-	12	pF	VCB=10V, f=1MHz, IE=0A

Classification Of hFE

Rank	A	B	C
hFE	100-250	160-400	250-630

Characteristics Curve



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